RD51 Activities At SINP

RD51 Group Applied Nuclear Physics Division Saha Institute of Nuclear Physics Kolkata, India

RD51 Mini Week CERN, 22-24 April, 2013

Ongoing RD51 Activities

Characterization Studies of Bulk Micromegas

- Measurement of detector characteristics (gain, energy resolution, electron transparency) and their dependence on detector design parameters and gas mixtures
- Simulation of detector characteristics to study the effect of different geometry modeling and components

Study of Ion Back Flow in Bulk Micromegas

• Measurement of IBF

Characterization Studies of Single GEM (to be extended to Triple-GEM)

- Simulation of field distribution and drift in single-GEM with staggered array of holes
- Numerical studies on the effect of etching in single-GEM

neBEM Upgrades

• Development of solid modeling in neBEM

Characterization Studies of Bulk Micromegas (Preliminary)



Measurements at SINP

Preliminary measurements for a new set of bulk Micromegas with different amplification gaps in P10 (no preconditioning done). Maximum gain achieved is higher for smaller gap.

10

450

500

550

Mesh Voltage in Volt

600

650

700

Characterization Studies of Bulk Micromegas (Preliminary)



Preliminary results show better resolution for larger gap at higher field with P10. 192 micron shows much worse resolution w.r.t earlier observation with Ar-Iso (90:10).

Characterization Studies of Bulk Micromegas (Preliminary)



Larger gap shows much better transparency at higher drift field.

Study of Ion Back Flow (IBF) in Bulk Micromegas (Preliminary)



Setup of IBF measurement at IRFU-Saclay

Study of Ion Back Flow (IBF) in Bulk Micromegas (Preliminary)



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Study of Ion Back Flow (IBF) in Bulk Micromegas (Preliminary)



IBF shows lower value for smaller gap except 64 micron case which exhibits the largest IBF.

Characterization Study of GEM (to be extended to Triple-GEM)



Regular array of holes

(Expt. Ref. Ph.D Thesis of G. Croci)



Collaboration Meeting, SBU Oct2012

Characterization Study of GEM (to be extended to Triple-GEM) (Preliminary)



GEM Device Staggered array of holes



Axial Field Distribution with Hole Array

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Characterization Study of GEM (to be extended to Triple-GEM) (**Preliminary**)

SVD versus LU in Periodic Array



LU-1x5

SVD-1x5

Transverse potential 10 micron above the upper surface

April 24, 2013

Characterization Study of GEM (to be extended to Triple-GEM)(Preliminary)Study on flourine etching in single-GEM



Perfect GEM



Etched GEM (Model A)



Etched GEM (Model B)





RD51 Mini Week, CERN

Characterization Study of GEM (to be extended to Triple-GEM) (**Preliminary**)



Gain distribution using MC method

Upgrade of neBEM

Development of solid modeler using BRL-CAD is underway.





X3D representation of a GEM

EUCLID representation of a GEM

EUCLID format in **BRL-CAD** will be opted for solid representation.

Future Plans

- Continuation of detailed characterization of Bulk Micromegas with different amplification gap using experimental and numerical investigations.
- Setup of well planned IBF test at Kolkata and its measurement in Micromegas.
- Initiation of experimental characterization of GEM and its extension to Triple-GEM.
- Continuation of numerical simulation of GEM and Triple-GEM in future to compare with experiments.
- Continuation of numerical simulation to study the effects of defects, artifacts and other components (spacer, frame) in Micromegas and GEM.
- Initiation of simulation on space charge and charging up effects.
- Development of solid modeler and interface of neBEM with GARFIELD++.

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